INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. **970607B**	Serial No. **10/050,169**
	Applicant(s): **Shinichiroh IKEMASU et al.**	
	Filing Date: **January 18, 2002**	Group Art Unit: **2814**

U.S. PATENT DOCUMENTS

Examiner Initial		Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
	AA	5,605,857	Jost et al.	02/97			
	AB	5,324,681	Lowrey et al.	06/94			
	AC	5,292,677	Dennison	03/94			
	AD	5,281,549	Fazan et al.	01/94			
	AE	5,760,429	Yano et al.	6/98			
	AF	5,479,054	Tottori	12/95			
	AG	5,150,278	Gonzalez et al.	9/92			
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
	AO						

OTHER DOCUMENTS

	AP	B.LUTHER et al.; Planar Copper-Polyimide Back End of the Line"; Proceedings of 10th International VMIC; pages 15-21; June 1993.
	AQ	B.M. SOMERO et al.; "A Modular in-situ Integration Scheme for Deep Submicron", Proceedings of 10th International VMIC; pages 28-34; June 1993.
	AR	M.F. CHISHOLM et al.; "A High Performance 0.5 um Five-Level Metal Process with Extendibility of Sub-Half Micron"; pages 22-28; June 1994.
	AS	M. RUTTEN et al.; "Pattern Density Effects in Tungsten CMP", Proceedings of 12th International VMIC; pages 491-497; June 1995.
	AT	I. NAIKI et al.; "Center Wordline Cell: A New Symmetric Layout Cell for 64Mb SRAM"; Technical Digest of IEDM; pages 817-820; December 1993.
	AU	T. KAGA et al.; "A 0.29-um2 MIM-Crown Cell and Process Technologies for 1-Gigabit DRAMs"; Technical Digest of IEDM; pages 927-929; December 1994.
	AV	H.K. KANG et al.; "Highly Manufacturable Process Technology for Reliable 256 Mbit and 1 Gbit DRAMs"; Technical Digest of IEDM; pages 635-638; December 1994.
	AW	Y. OHJI et al.; "Ta_2O_5 Capacitors Dielectric Material for Giga-bit DRAMs"; Technical Digest of IEDM; pages 111-114; December 1995.
	AX	Y. NISHIOKA et al.; "Giga-bit Scale DRAM Cell with New Simple Ru/(Ba,Sr)TiO3/Ru Stacked Capacitors Using X-ray Lithography"; Technical Digest of IEDM; pages 903-906; December 1995.
	AY	K.P. LEE et al.; "A Process Technology for 1 Giga-bit DRAM"; Technical Digest of IEDM; pages 907-910; December 1995.
	AZ	J.K. PARK et al.; "Isolation Merged Bit Line Cell(IMBC) for 1Gb DRAM and Beyond". Technical Digest of IEDM; pages 911-914; December 1995.
	BA	
	BB	

Examiner _____ Date Considered 6/17/04